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Kind regards,

Team Nexperia



40 V, 200 mA PNP/PNP general-purpose double transistorRev. 02 — 13 May 2009Product data set

Product data sheet

1. Product profile

1.1 General description

PNP/PNP general-purpose double transistor in a SOT363 (SC-88) very small Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number				NPN/PNP	Package
	NXP	JEITA	complement	complement	configuration
PMBT3906YS	SOT363	SC-88	PMBT3904YS	PMBT3946YPN	very small

1.2 Features

- General-purpose double transistor
- Board-space reduction
- AEC-Q101 qualified

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 2. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V _{CEO}	collector-emitter voltage	open base	-	-	-40	V
I _C	collector current		-	-	-200	mA
h _{FE}	DC current gain	V _{CE} = -1 V; I _C = -10 mA	100	180	300	



40 V, 200 mA PNP/PNP general-purpose double transistor

Pinning information 2.

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		
2	base TR1		
3	collector TR2		
4	emitter TR2		
5	base TR2		
6	collector TR1		1 2 3
			sym018

Ordering information 3.

Table 4. Orde	Table 4. Ordering information				
Type number Packag					
	Name	Description	Version		
PMBT3906YS	SC-88	plastic surface-mounted package; 6 leads	SOT363		

Marking 4.

Table 5. M	arking codes	
Type numbe	r	Marking code ^[1]
PMBT3906YS	3	BD*
	-	

[1] * = -: made in Hong Kong

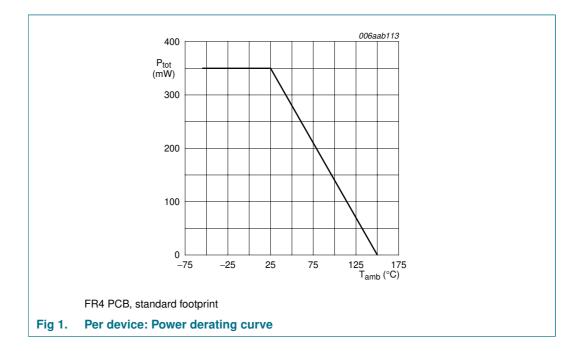
- * = p: made in Hong Kong * = t: made in Malaysia
- * = W: made in China

40 V, 200 mA PNP/PNP general-purpose double transistor

5. Limiting values

Table 6. Limiting values In accordance with the Absolute Maximum Rating System (IEC 60134).					
Symbol	Parameter	Conditions	Min	Мах	Unit
Per transistor					
V _{CBO}	collector-base voltage	open emitter	-	-40	V
V _{CEO}	collector-emitter voltage	open base	-	-40	V
V _{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-200	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-200	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	230	mW
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	350	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

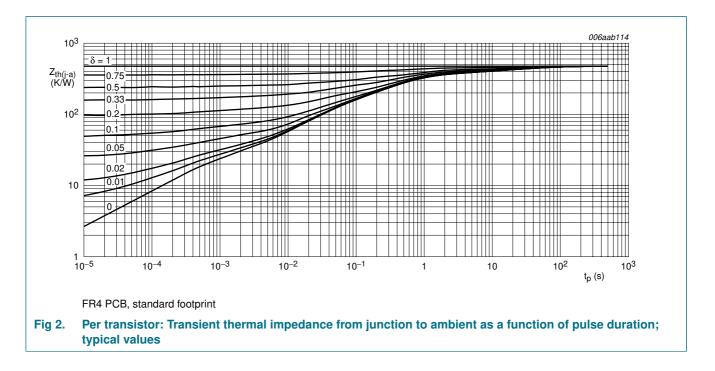


40 V, 200 mA PNP/PNP general-purpose double transistor

6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	543	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	290	K/W
Per device						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



40 V, 200 mA PNP/PNP general-purpose double transistor

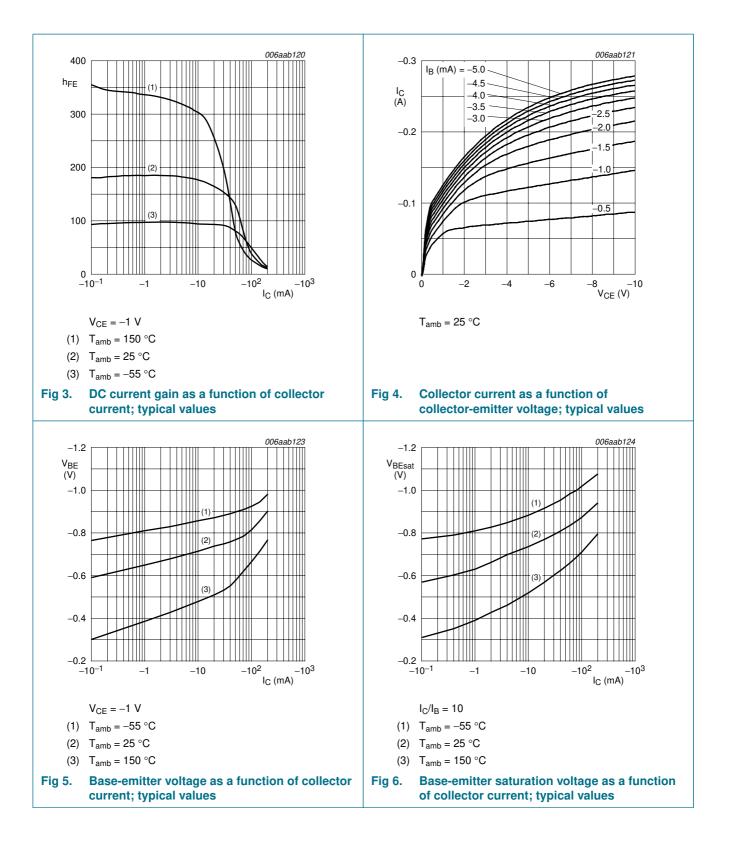
7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$	-	-	-50	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -6 \text{ V; } I_C = 0 \text{ A}$	-	-	-50	nA
h _{FE}	DC current gain	$V_{CE} = -1 V$				
		$I_{\rm C} = -0.1 \rm{mA}$	60	180	-	
		$I_{\rm C} = -1 \rm{mA}$	80	180	-	
		$I_{\rm C} = -10 \text{ mA}$	100	180	300	
		I _C = -50 mA	60	130	-	
		I _C = -100 mA	30	50	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -1 \text{ mA}$	-	-100	-250	mV
		$I_{C} = -50 \text{ mA};$ $I_{B} = -5 \text{ mA}$	-	-165	-400	mV
V _{BEsat} base-emitter saturation voltage	base-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -1 \text{ mA}$	-	-750	-850	mV
		$I_{C} = -50 \text{ mA};$ $I_{B} = -5 \text{ mA}$	-	-850	-950	mV
f _T	transition frequency	V _{CE} = -20 V; I _C = -10 mA; f = 100 MHz	250	-	-	MHz
C _c	collector capacitance		-	-	4.5	pF
C _e	emitter capacitance	$\label{eq:VBE} \begin{array}{l} V_{BE} = -0.5 \ V; \\ I_C = i_c = 0 \ A; \\ f = 1 \ MHz \end{array}$	-	-	10	pF
NF	noise figure	$\label{eq:VCE} \begin{array}{l} V_{CE} = -5 \ V; \\ I_{C} = -100 \ \mu A; \\ R_{S} = 1 \ k \Omega; \\ f = 10 \ Hz \ to \ 15.7 \ kHz \end{array}$	-	-	4	dB
t _d	delay time	$V_{CC} = -3 V;$	-	-	35	ns
t _r	rise time	I _C = -10 mA; I _{Bon} = -1 mA;	-	-	35	ns
t _{on}	turn-on time	$I_{Bon} = -1 \text{ mA},$ $I_{Boff} = 1 \text{ mA}$	-	-	70	ns
t _s	storage time		-	-	225	ns
t _f	fall time		-	-	75	ns
t _{off}	turn-off time		-	-	300	ns

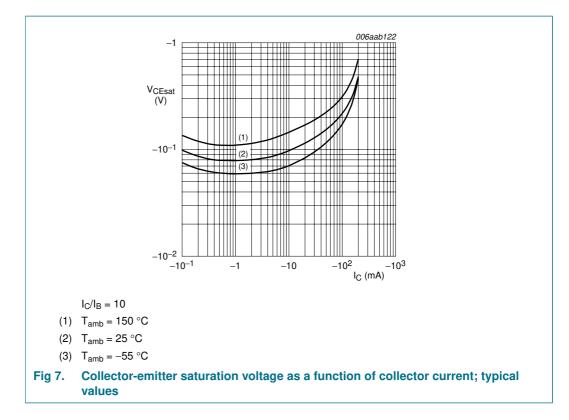
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PMBT3906YS

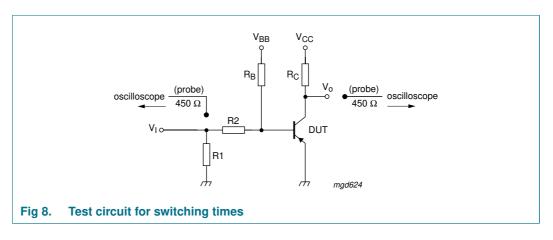
40 V, 200 mA PNP/PNP general-purpose double transistor



40 V, 200 mA PNP/PNP general-purpose double transistor



8. Test information

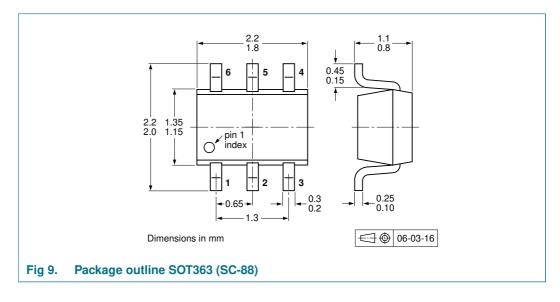


8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

40 V, 200 mA PNP/PNP general-purpose double transistor

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity	
				3000	10000
PMBT3906YS	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	<u>[3]</u>	-125	-165

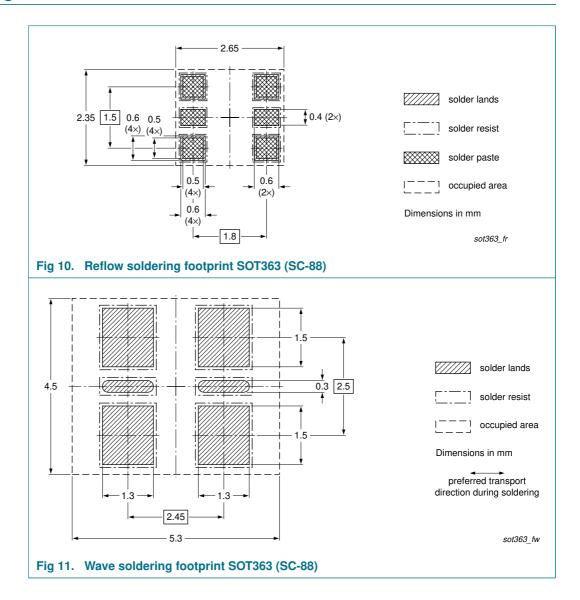
[1] For further information and the availability of packing methods, see <u>Section 14</u>.

[2] T1: normal taping

[3] T2: reverse taping

40 V, 200 mA PNP/PNP general-purpose double transistor

11. Soldering



40 V, 200 mA PNP/PNP general-purpose double transistor

12. Revision history

Table 10.Revision his	tory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBT3906YS_2	20090513	Product data sheet	-	PMBT3906YS_1
Modifications:	 Figure 4: an 	nended		
PMBT3906YS_1	20080306	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PMBT3906YS

40 V, 200 mA PNP/PNP general-purpose double transistor

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